

MSAEZ50N10A
MSAFZ50N10A

Features

- Ultrafast rectifier in parallel with the body diode (MSAE type only)
- Rugged polysilicon gate cell structure
- Increased Unclamped Inductive Switching (UIS) capability
- Hermetically sealed, surface mount power package
- Low package inductance
- Very low thermal resistance
- Reverse polarity available upon request

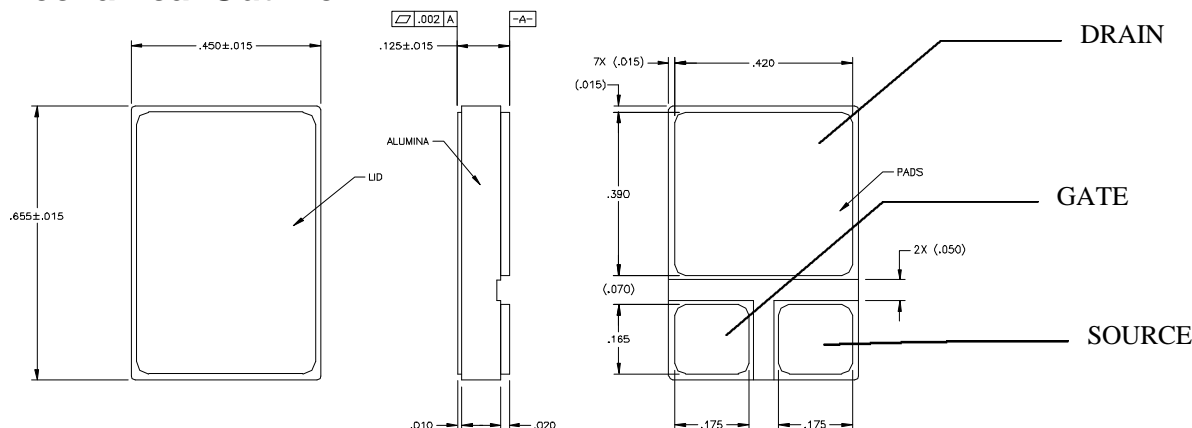
100 Volts
50 Amps
35 mΩ

N-CHANNEL
ENHANCEMENT MODE
POWER MOSFET

Maximum Ratings @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	MAX.	UNIT
Drain-to-Source Breakdown Voltage (Gate Shorted to Source) @ T _J ≥ 25°C	BV _{DSS}	100	Volts
Drain-to-Gate Breakdown Voltage @ T _J ≥ 25°C, R _{GS} = 1 MΩ	BV _{DGR}	100	Volts
Continuous Gate-to-Source Voltage	V _{GS}	+/-20	Volts
Transient Gate-to-Source Voltage	V _{GSM}	+/-30	Volts
Continuous Drain Current 100°C	I _{D25} I _{D100}	50 40	Amps
Peak Drain Current, pulse width limited by T _{Jmax}	I _{DM}	200	Amps
Repetitive Avalanche Current	I _{AR}	50	Amps
Repetitive Avalanche Energy	E _{AR}	18.5	mJ
Single Pulse Avalanche Energy	E _{AS}	400	mJ
Voltage Rate of Change of the Recovery Diode @ I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	dv/dt	TBD	V/ns
Power Dissipation	P _D	300	Watts
Junction Temperature Range	T _J	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Continuous Source Current (Body Diode)	I _S	50	Amps
Pulse Source Current (Body Diode)	I _{SM}	200	Amps
Thermal Resistance, Junction to Case	θ _{JC}	0.4	°C/W

Mechanical Outline



MSAEZ50N10A MSAFZ50N10A

Electrical Parameters @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Drain-to-Source Breakdown Voltage (Gate Shorted to Source)	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	100			V
Temperature Coefficient of the Drain-to-Source Breakdown Voltage	$\Delta BV_{DSS}/\Delta T_J$			TBD		V/°C
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\ \text{mA}$	2.0	3.0	4.0	V
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}_{DC}, V_{DS} = 0\ \text{T}_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			± 100 ± 200	nA
Drain-to-Source Leakage Current (Zero Gate Voltage Drain Current)	I_{DSS}	$V_{DS} = 0.8 \cdot BV_{DSS}\ \text{T}_J = 25^\circ\text{C}$ $V_{GS} = 0\ \text{T}_J = 125^\circ\text{C}$			25 250	μA
Static Drain-to-Source On-State Resistance (1)	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 32\ \text{T}_J = 25^\circ\text{C}$ $I_D = 50\ \text{T}_J = 25^\circ\text{C}$ $I_D = 32\ \text{T}_J = 125^\circ\text{C}$		0.03 TBD 0.05	0.035	Ω
Forward Transconductance (1)	g_{fs}	$V_{DS} \geq 15\ \text{V}; I_D = 32\ \text{A}$	15	28		S
Input Capacitance	C_{iss}	$V_{GS} = 0\ \text{V}, V_{DS} = 25\ \text{V}, f = 1\ \text{MHz}$		2400	3200	pF
Output Capacitance	C_{oss}			730	1100	
Reverse Transfer Capacitance	C_{rss}			430	650	
Turn-on Delay Time	$T_{d(on)}$	$V_{GS} = 10\ \text{V}, V_{DS} = 30\ \text{V},$ $I_D = 3\ \text{A}, R_G = 50\ \Omega$		33	50	ns
Rise Time	t_r			140	210	
Turn-off Delay Time	$t_{d(off)}$			500	670	
Fall Time	t_f			230	310	
Total Gate Charge	$Q_{g(on)}$	$V_{GS} = 10\ \text{V}, V_{DS} = 80\text{V}, I_D = 30\text{A}$		225		nC
Gate-to-Source Charge	Q_{gs}			20		
Gate-to-Drain (Miller) Charge	Q_{gd}			100		
Body Diode Forward Voltage (1)	V_{SD}	$I_F = I_S, V_{GS} = 0\ \text{V}$			1.2 1.8	V
Reverse Recovery Time (Body Diode)	t_{rr}	$I_F = 10\ \text{A},$ $-di/dt = 100\ \text{A}/\mu\text{s},$	MSAE		50	ns
			MSAF		170	
Reverse Recovery Charge	Q_{rr}	$I_F = 10\ \text{A},$ $di/dt = 100\ \text{A}/\mu\text{s},$			tbd 0.9	μC

Notes

- (1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\delta \leq 2\%$
- (2) Microsemi Corp. does not manufacture the mosfet die; contact company for details.